

## AO5600E-VB Datasheet

### N-and P-Channel 20V (D-S) MOSFET

#### PRODUCT SUMMARY

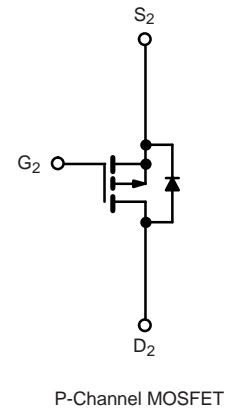
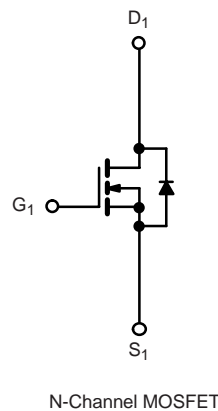
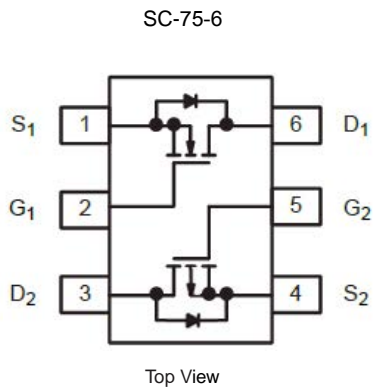
	$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
N-Channel	20	0.270 at $V_{GS} = 4.5$ V	0.60
		0.410 at $V_{GS} = 2.5$ V	0.55
P-Channel	- 20	0.660 at $V_{GS} = - 4.5$ V	- 0.30
		0.840 at $V_{GS} = - 2.5$ V	- 0.25

#### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



#### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V <sub>DS</sub>	20	- 20	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	0.6	- 0.3	A
	T <sub>A</sub> = 70 °C		0.55	- 0.25	
Pulsed Drain Current		I <sub>DM</sub>	3	- 2	
Continuous Source Current (Diode Conduction) <sup>a, b</sup>		I <sub>S</sub>	1.05	- 1.05	
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.15		W
	T <sub>A</sub> = 70 °C		0.73		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	93	110	$^\circ\text{C/W}$
		130	150	
Maximum Junction-to-Lead	$R_{thJL}$	75	90	

Notes:

a. Surface Mounted on FR4 board.

b.  $t \leq 5$  s.

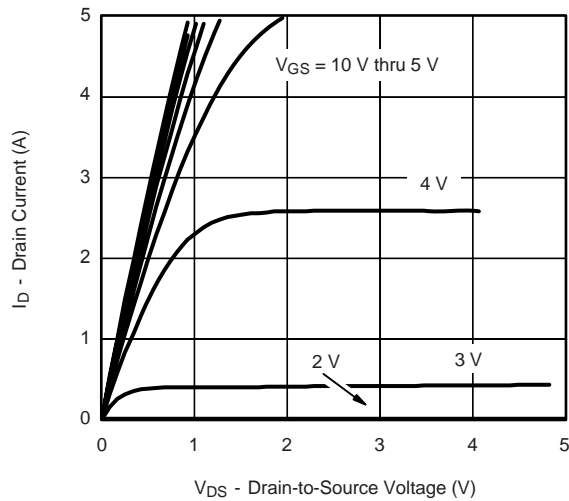
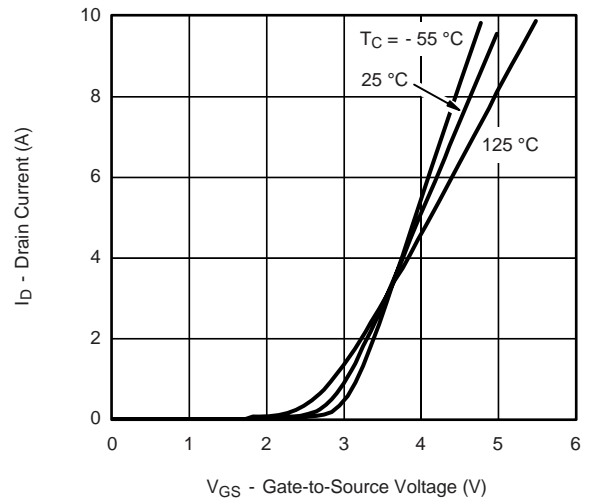
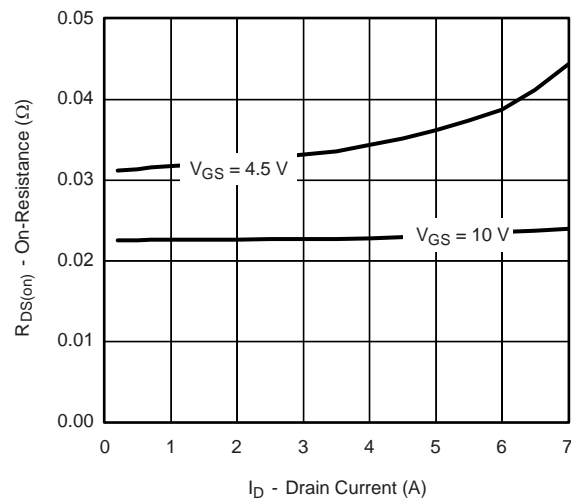
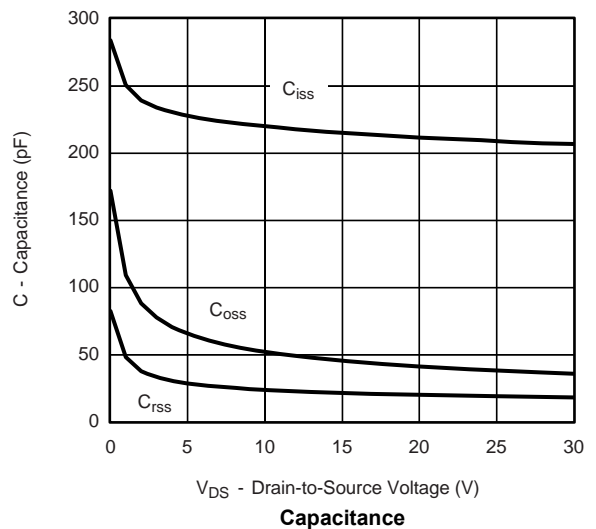
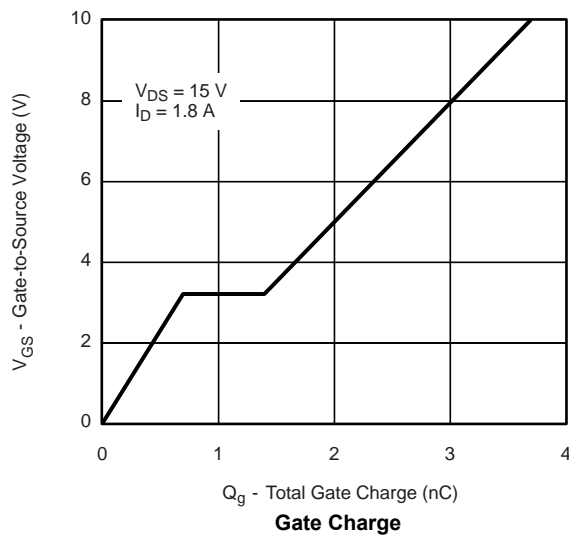
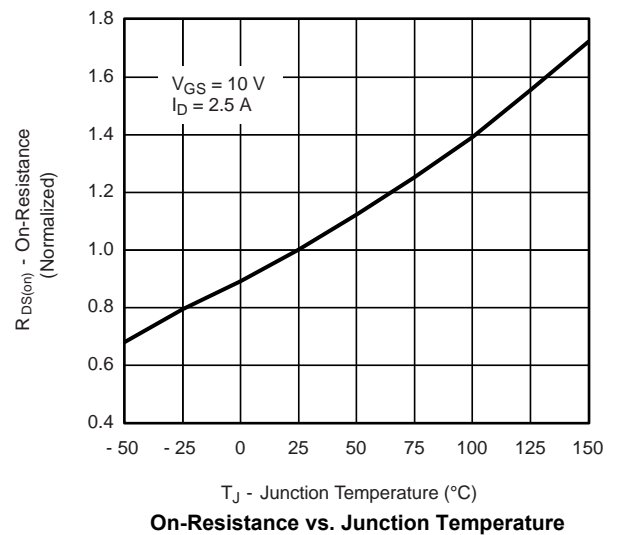
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.7			V	
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	- 0.8				
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch P-Ch			$\pm 100$ $\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	$\mu\text{A}$	
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			- 1		
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$	N-Ch			5		
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$	P-Ch			- 5		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	3.7			A	
		$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	- 3				
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 2.5\text{ V}, I_D = 0.6\text{ A}$	N-Ch		0.410		$\Omega$	
		$V_{GS} = -2.5\text{ V}, I_D = -0.3\text{ A}$	P-Ch		0.840			
		$V_{GS} = 4.5\text{ V}, I_D = 0.6\text{ A}$	N-Ch		0.270			
		$V_{GS} = -4.5\text{ V}, I_D = -0.3\text{ A}$	P-Ch		0.660			
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$	N-Ch		4.3		S	
		$V_{DS} = -15\text{ V}, I_D = -1.8\text{ A}$	P-Ch		2.4			
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.05\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.81	1.10	V	
		$I_S = -1.05\text{ A}, V_{GS} = 0\text{ V}$	P-Ch		- 0.83	- 1.10		
Dynamic <sup>b</sup>								
Total Gate Charge	$Q_g$	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 1.8\text{ A}$	N-Ch P-Ch		2.1 2.4	3.2 3.6	nC	
Gate-Source Charge	$Q_{gs}$		N-Ch P-Ch		0.7 0.9			
Gate-Drain Charge	$Q_{gd}$	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = -5\text{ V}, I_D = -1.8\text{ A}$	N-Ch P-Ch		0.7 0.8			
Gate Resistance	$R_g$			N-Ch P-Ch	0.5 3		2.4 11	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch P-Ch		7 8	11 12	ns	
Rise Time	$t_r$		N-Ch P-Ch		9 12	14 18		
Turn-Off Delay Time	$t_{d(off)}$		P-Channel $V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch P-Ch		13 12		20 18
				N-Ch P-Ch		5 7		8 11
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.05\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$	N-Ch		35	60		
		$I_F = -1.05\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$	P-Ch		30	60		

Notes:

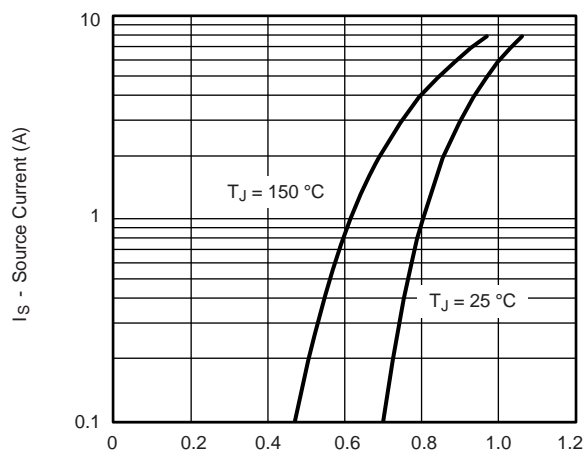
a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

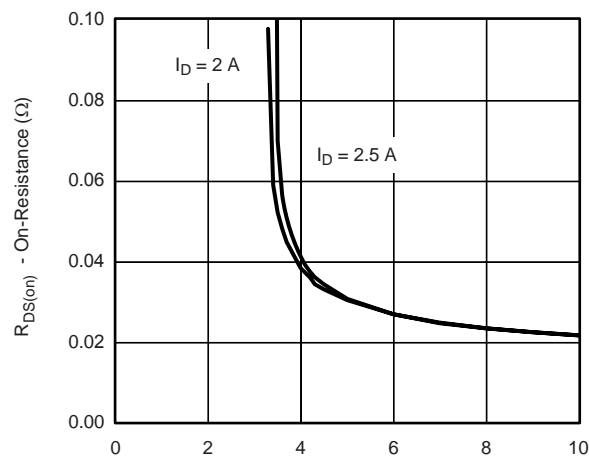
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

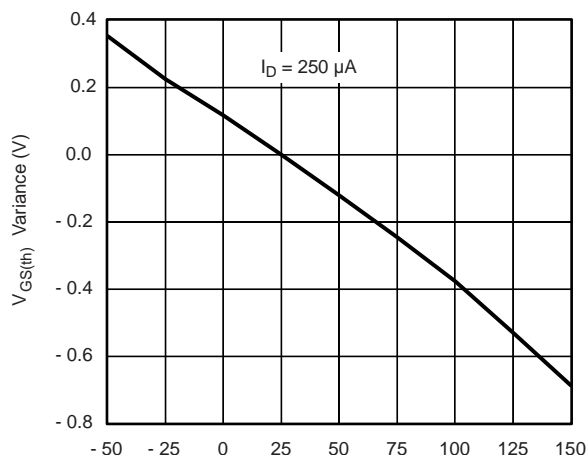
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



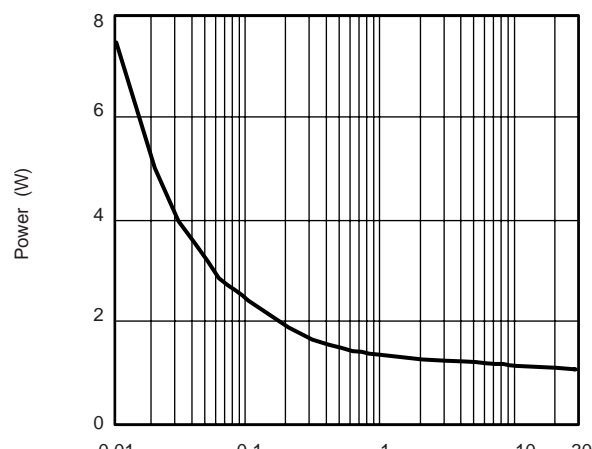
Source-Drain Diode Forward Voltage



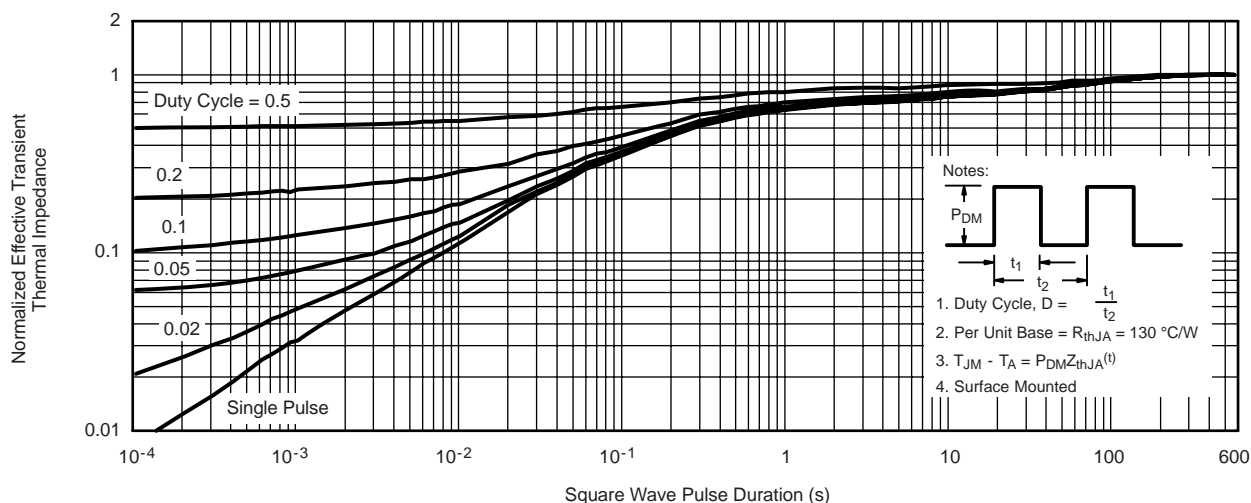
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

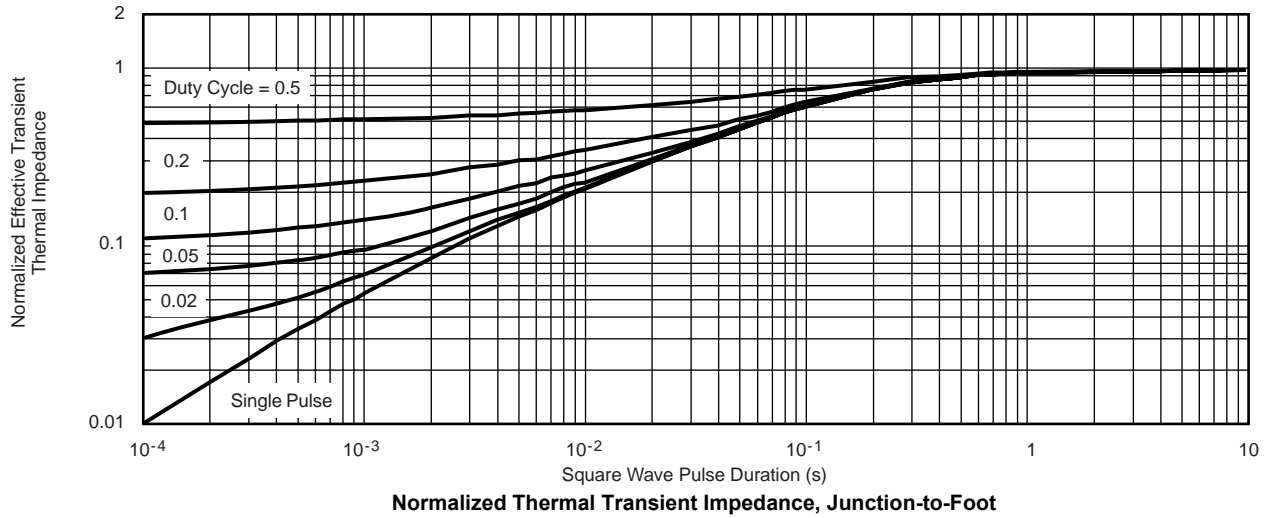


Single Pulse Power (Junction-to-Ambient)

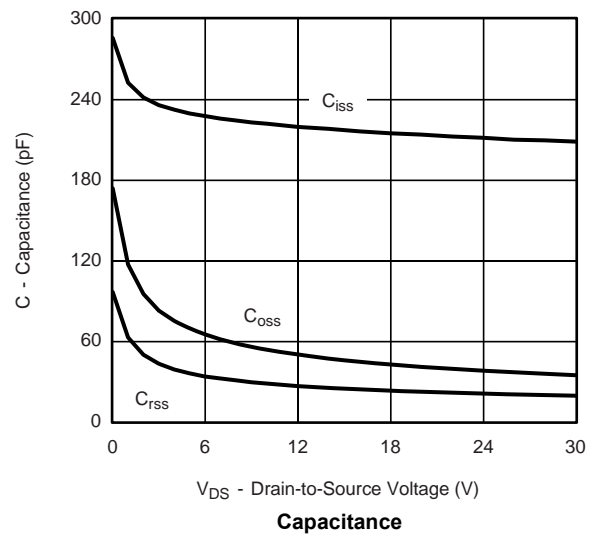
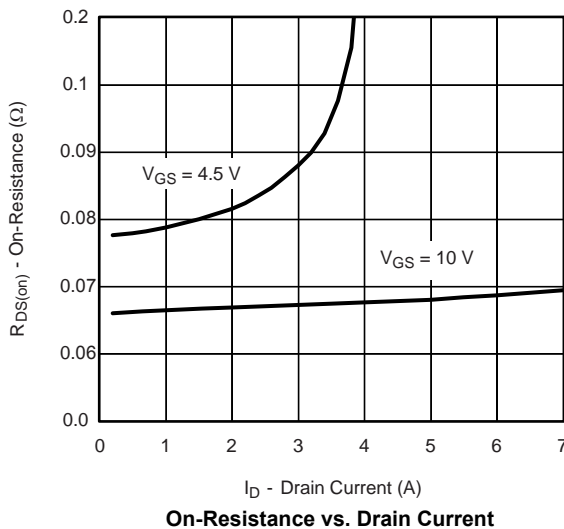
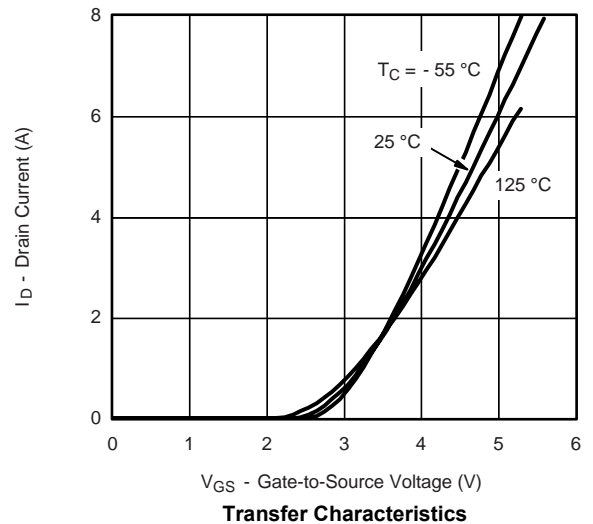
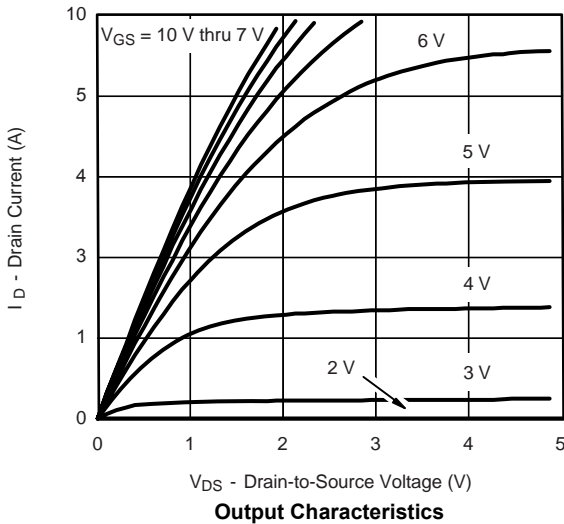


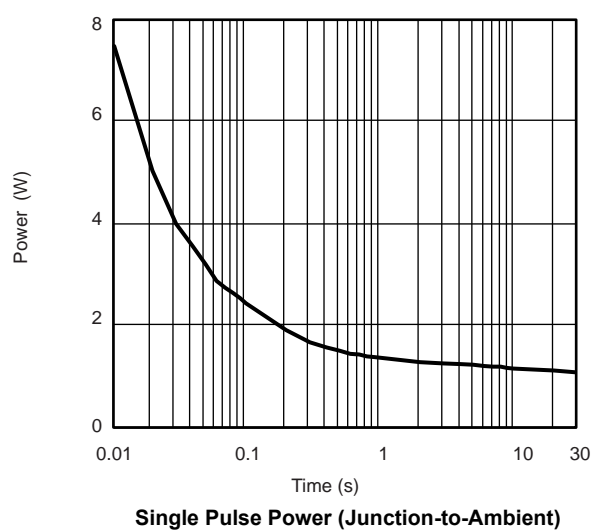
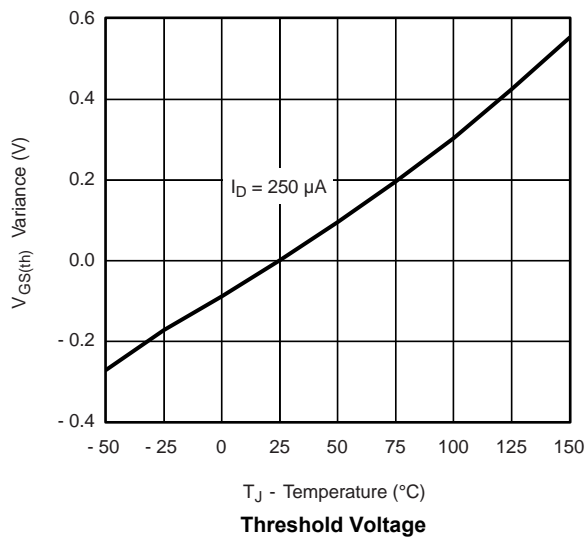
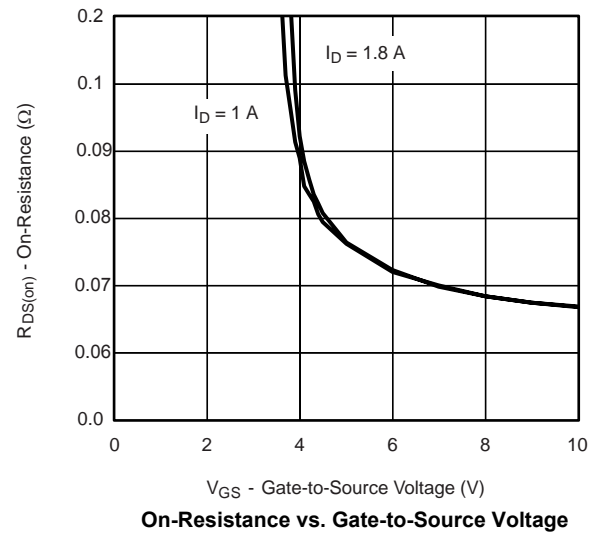
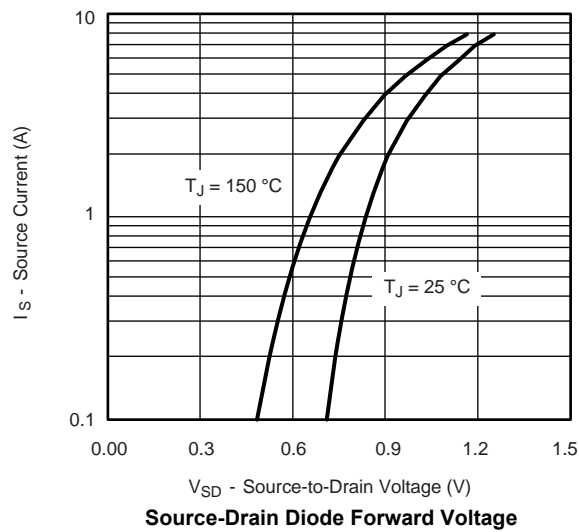
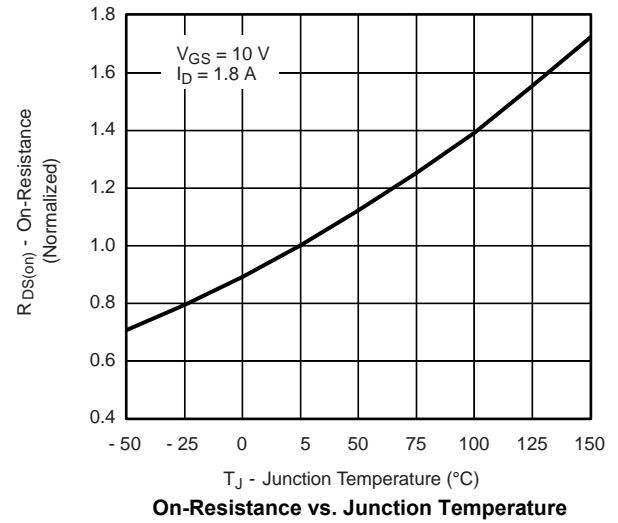
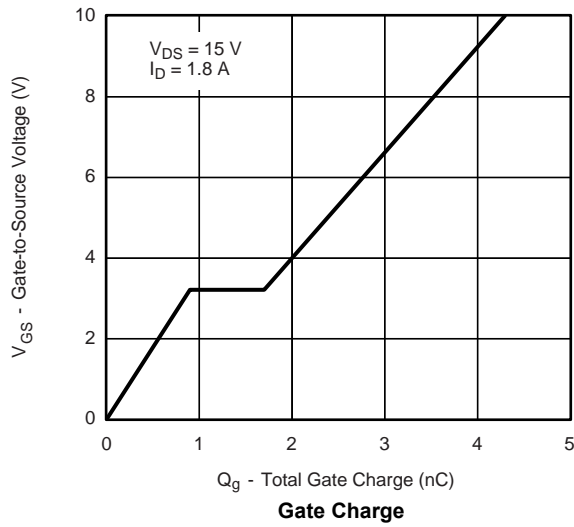
Normalized Thermal Transient Impedance, Junction-to-Ambient

**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

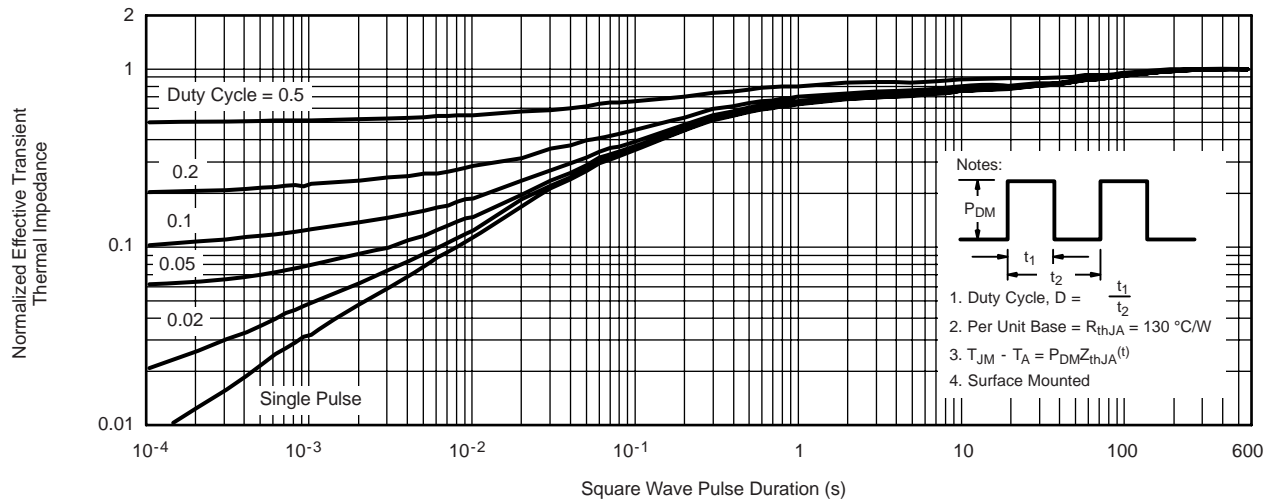


**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

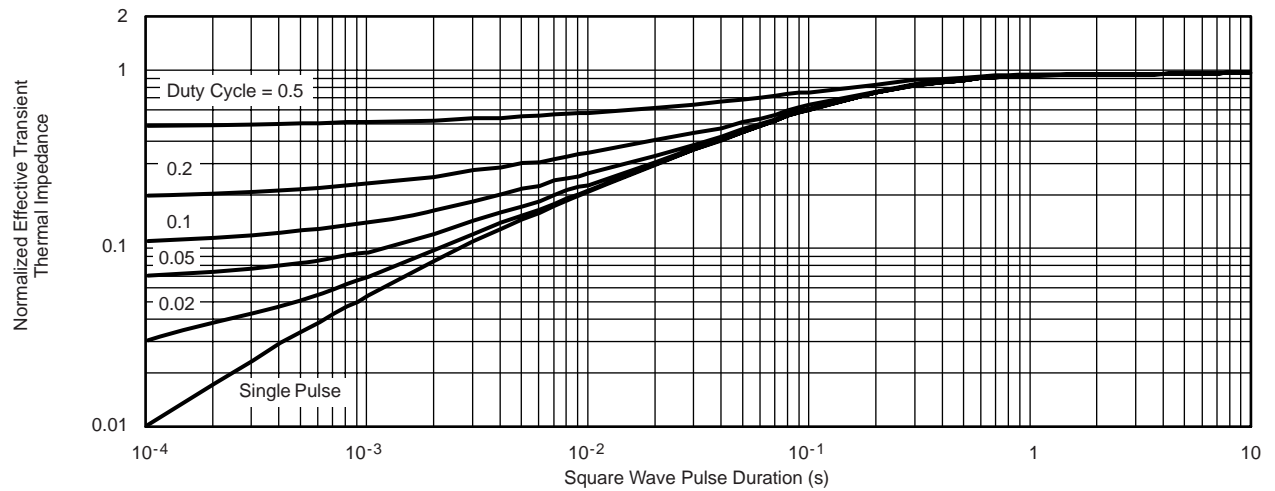


**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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